

# JIEJIE MICROELECTRONICS CO., LTD.

---

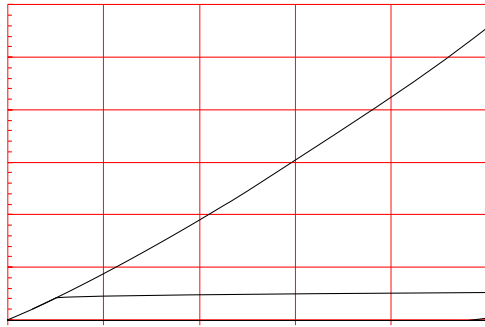
## JCT816CH

 JieJie Microelectronics Co., Ltd.

|                                              |             |    |   |
|----------------------------------------------|-------------|----|---|
| Average gate power dissipation ( $T_j=150$ ) | $P_{G(AV)}$ | 1  | W |
| Peak gate power                              | $P_{GM}$    | 20 | W |

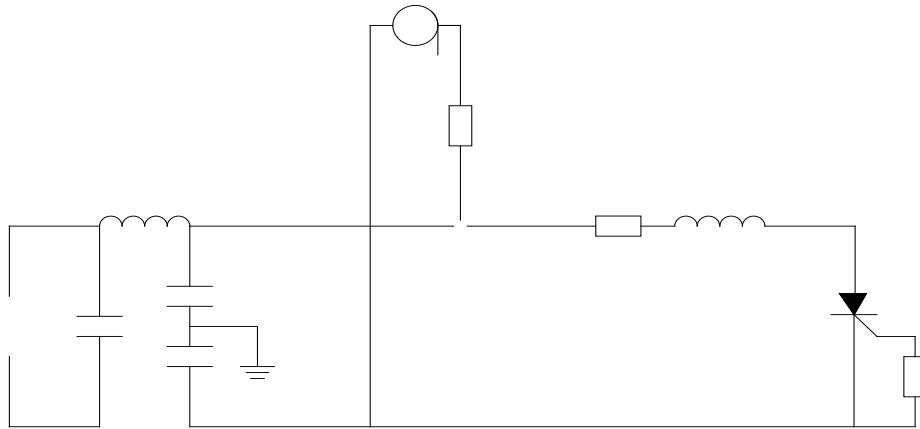
JCT816CH  
JieJie Microelectronics Co., Ltd.

**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



| Order code | Voltage<br>$V_{\text{DRM}}/V_{\text{RRM}}$ (V) | IGT(mA) | Package | Base qty.<br>(pcs) | Delivery<br>mode |
|------------|------------------------------------------------|---------|---------|--------------------|------------------|
| JCT816CH   | 800                                            | 15      | TO-220C | 50                 | Tube             |

**Document Revision History**

| Date         | Revision | Changes |
|--------------|----------|---------|
| Jun.15, 2023 | A.       |         |



Information furnished in this document is believed to be accurate and reliable.  
However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the  
consequences of use without consideration for such information nor use beyond it.

Howconi

rd

ratform(m)-3

(at)2